UNITED STATES PATENT AND TRADEMARK OFFICE **CERTIFICATE OF CORRECTION**

PATENT NO.

: 7,052,623 B1

Page 1 of 1

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INVENTOR(S)

: Volker Becker et al.

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Column 1, line 24, change "Disadvantages" to -- Disadvantageous--

Column 1, line 33, change "can act very" to --can act very corrosively.--

Column 3, line 12, change "....OF THE DRAWING" to --OF THE **DRAWINGS--**

Column 6, line 13, change "in which the. silicon" to --in which the silicon--

Column 7, line 16, change "DE 42 41 045, and" to --DE 42 41 045, an-

Column 7, line 32, change "remain essentially" to --remain essentially unchanged .--

Column 11, line 54, change "etching process than etching" to --etching process then etching--

Column 12, line 40, change "layer section 912)" to --layer section (12)--

Column 16, line 18, change "is formed thermally grown silicon" to --is formed from thermally grown silicon--

Signed and Sealed this

Twenty-second Day of May, 2007

JON W. DUDAS Director of the United States Patent and Trademark Office